

10A/100V 耐压 N 沟道增强型场效应管

产品概述

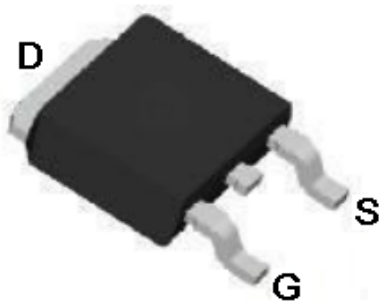
V_{DSS}	I_D	$R_{DS(ON)}(m\Omega)TYP$
100V	10A	85@ $V_{GS}=10, I_D=4.5A$

产品特点

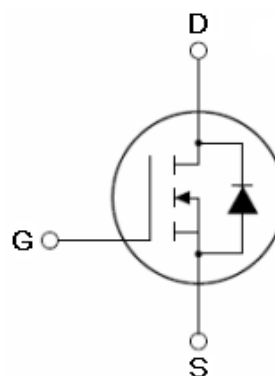
- 低导通电阻
- 高可靠性
- 驱动要求简单
- 采用 TO-252

封装

- 封装示意图



To-252 Top View



Schematic Diagram

订购信息

产品型号	储存温度	封装形式	Devices Per Reel
LN10N10	-55°C to +150°C	TO-252	-

绝对最大额定值

($T_A=25^\circ\text{C}$, 除非特别说明)

参数	符号	极限值	单位
最大漏源电压	V_{DS}	100	V
最大栅源电压	V_{GS}	± 20	V
结温 25°C , 最大漏极电流	I_D	10	A
结温 100°C , 最大漏极电流	I_D	8.5	A
最大漏极脉冲电流	I_{DM}	56	A
最大消耗功耗 ($P_c=25^\circ\text{C}$)	P_D	28	W
工作温度范围	T_j	-55—150	$^\circ\text{C}$

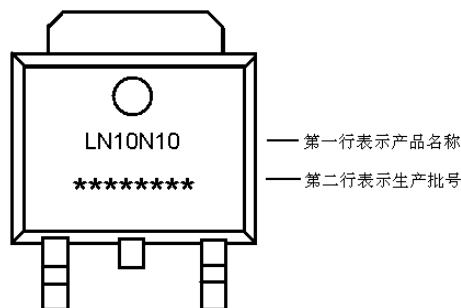
■ 电气特性

(TA=25°C unless otherwise noted)

参数	符号	条件	最小	典型	最大	单位
关态特性						
漏源击穿电压	BVDSS	VGS=0V, ID=250μA	100			V
零栅压漏电流	IDSS	VDS=100V, VGS=0V			1	μA
栅-衬漏电流	IGSS	VDS=0V, VGS=±20V			±100	nA
开态特性						
栅极阈值电压	VGS(th)	VDS=VGS, ID=250μA	1.5	2.0	2.6	V
漏源通态电阻	RDS(ON)	VGS=10V, ID=4.5A		85	95	mΩ
正向跨导	gfs	VDS=5V, ID=4.5A	5			S
动态参数						
输入电容	CISS	VDS=50V, VGS=0V f=1.0MHz		612		pF
输出电容	COSS			120		
反向传输电容	CRSS			91		
开关特性						
开通延迟时间	tD(ON)	VDD=50V RL=8.6ohm VGS=10V RGEN=3ohm		8		ns
上升时间	tr			3		
关断延迟时间	tD(OFF)			17		
下降时间	tf			4.5		
栅极总电荷	Qg	VDS=50V, ID=4.5A VGS=10V		11		nC
栅源电荷	Qgs			1.9		
栅漏电荷	Qgd			2.8		
漏源二极管特征参数						
漏源二极管正向电压	VSD	VGS=0V, Isd=1 A		0.7	1	V

■ 温度特性

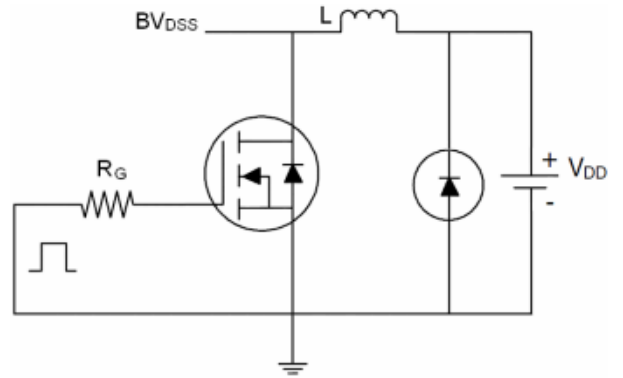
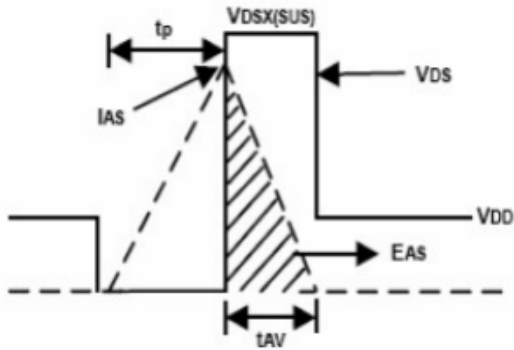
热电阻 结温-环境温度	Rth JA	3.3	°C/W
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■ 打印标识


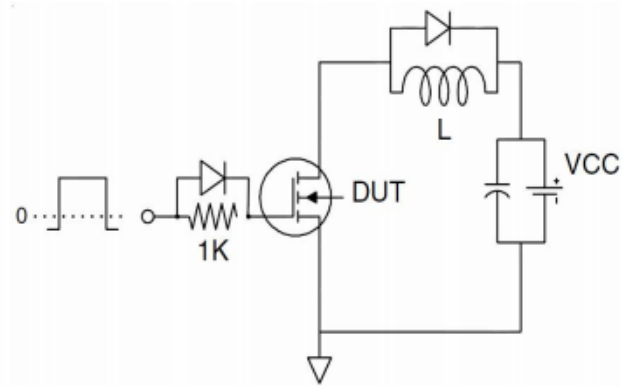
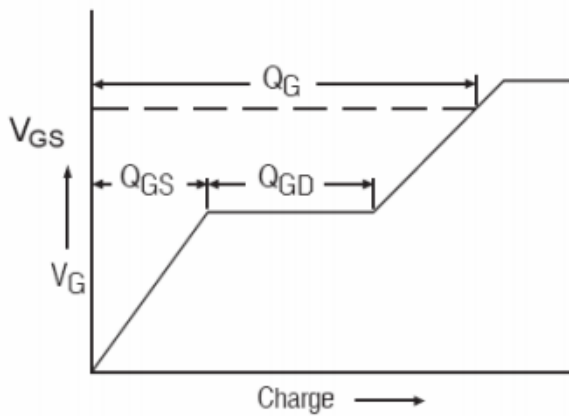
测试电路与特性曲线

- 测试电路图

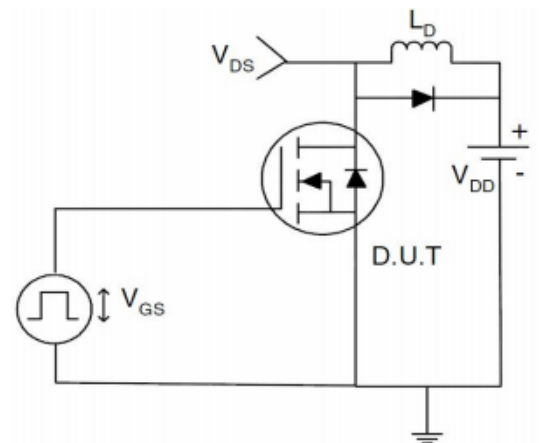
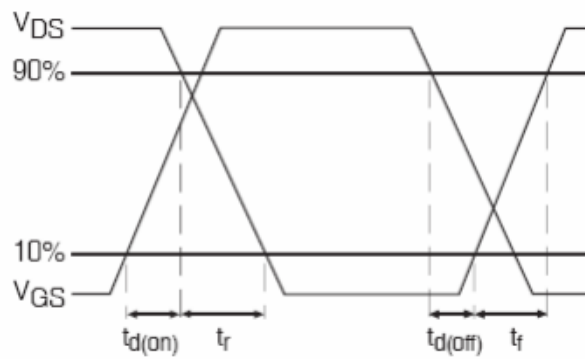
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit:



3) Switch Time Test Circuit:



● 测试电路图

Figure1. On-Region Characteristics

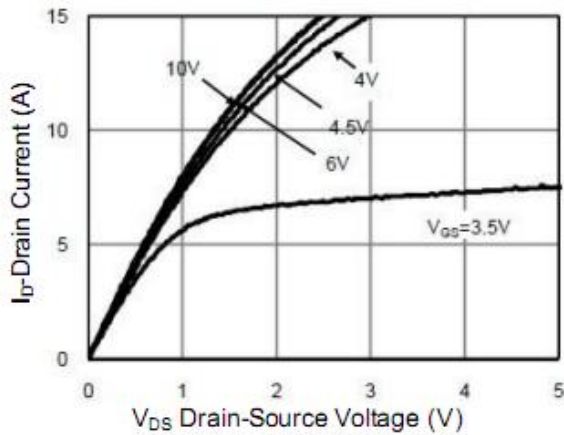


Figure 2: Transfer Characteristics

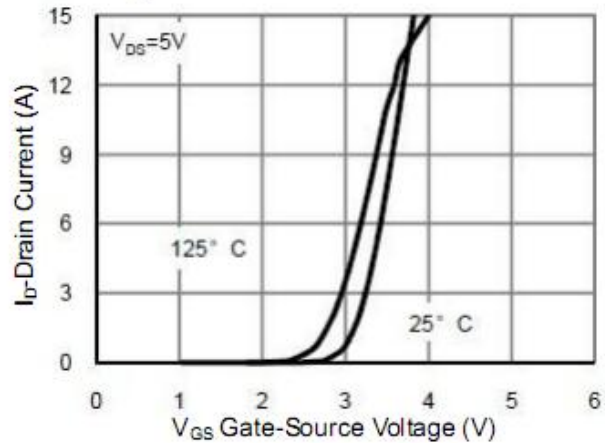


Figure3. On-Resistance vs. Drain Current and Gate Voltage

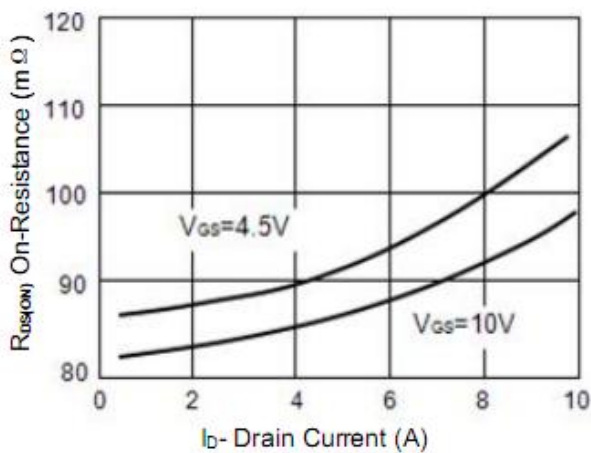


Figure4. On-Resistance vs. Junction Temperature

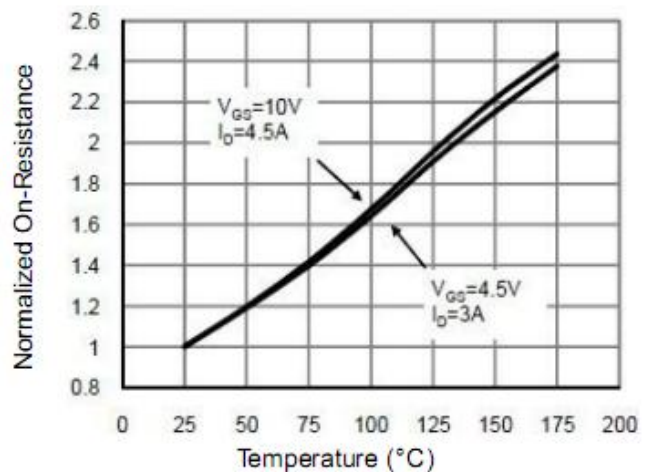


Figure5. On-Resistance vs. Gate-Source Voltage

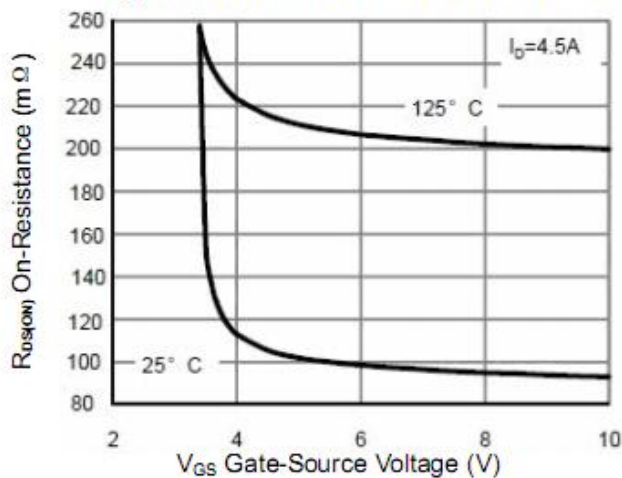


Figure6. Body-Diode Characteristics

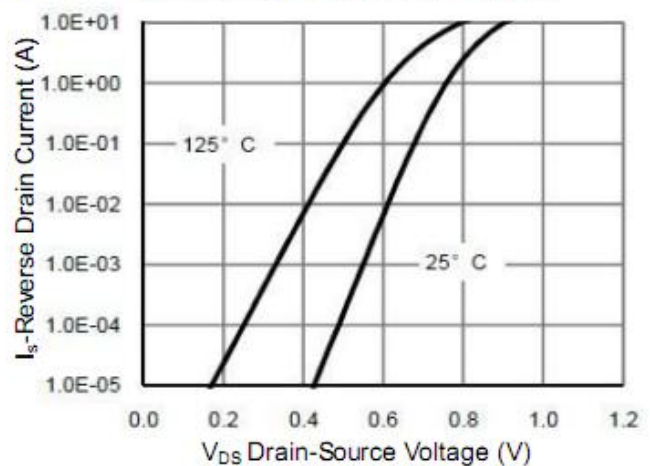


Figure 7. Gate-Charge Characteristics

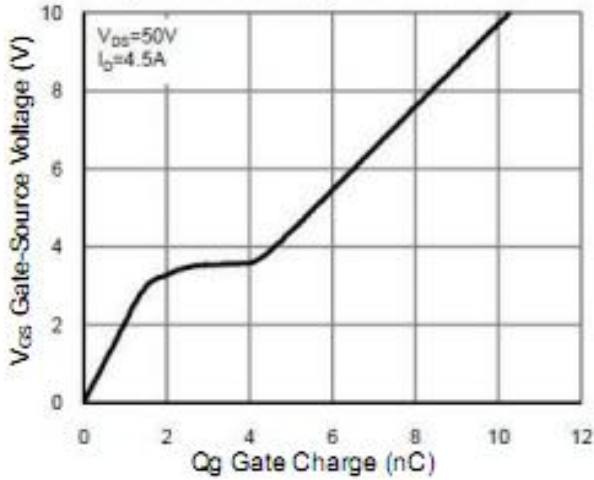


Figure 8. Capacitance Characteristics

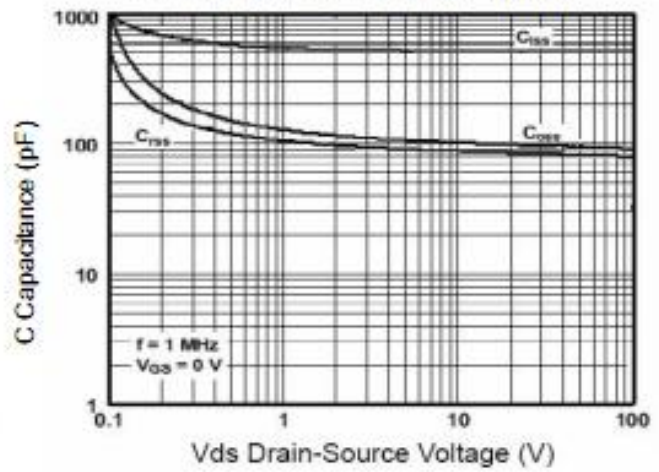


Figure 9. Maximum Forward Biased Safe Operating Area

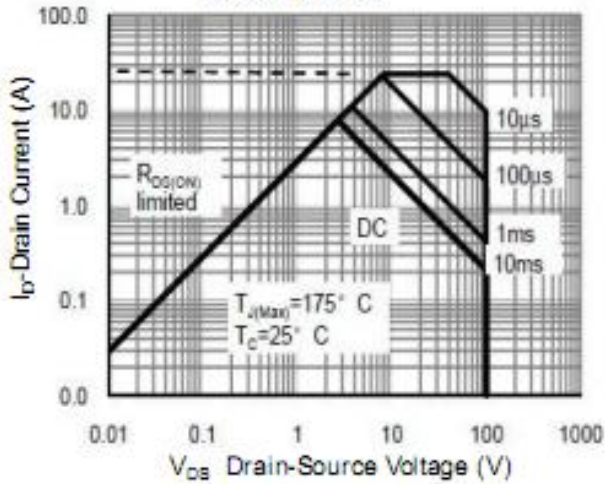


Figure 10. Single Pulse Power Rating Junction-to-Case

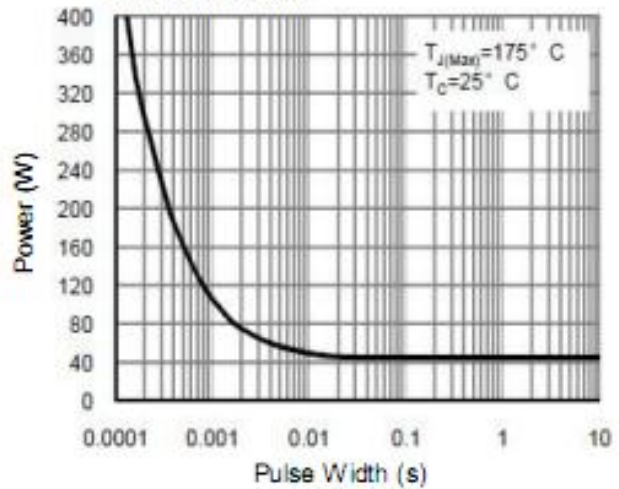
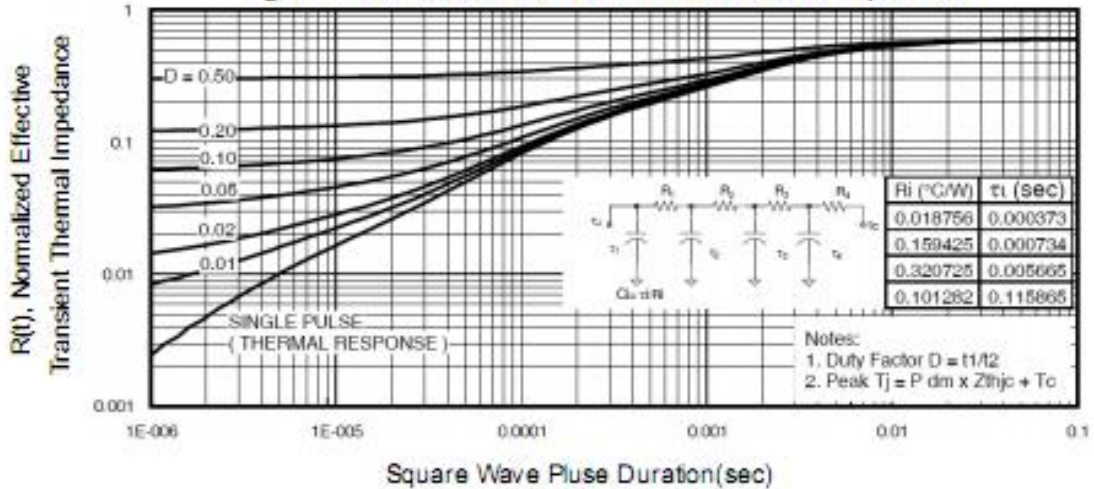
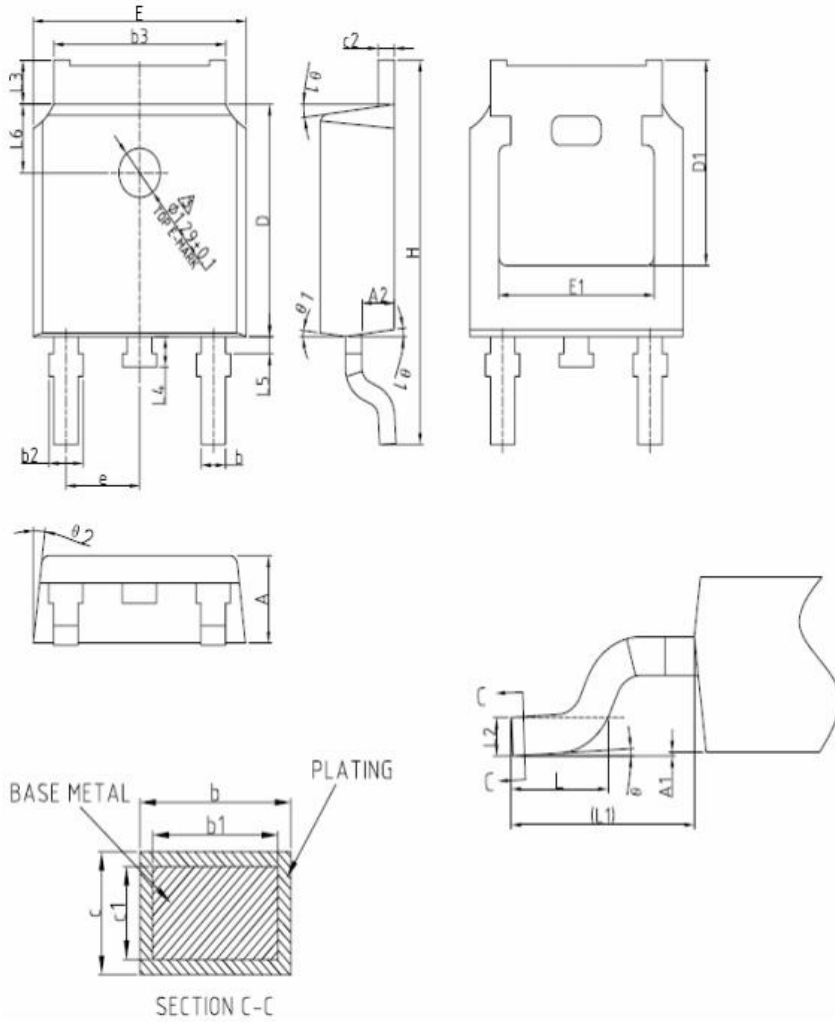


Figure 11. Normalized Maximum Transient Thermal Impedance



封装形式

- TO-252



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	2.20	2.30	2.38
A1	0	-	0.10
A2	0.90	1.01	1.10
b	0.72	-	0.85
b1	0.71	0.76	0.81
b2	0.72	-	0.90
b3	5.13	5.33	5.46
c	0.47	-	0.60
c1	0.46	0.51	0.56
c2	0.47	-	0.60
D	6.00	6.10	6.20
D1	5.25	-	-
E	6.50	6.60	6.70
E1	4.70	-	-
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90REF		
L2	0.51BSC		
L3	0.90	-	1.25
L4	0.60	0.80	1.00
L5	0.15	-	0.75
L6	1.80REF		
θ	0°	-	8°
θ 1	5°	7°	9°
θ 2	5°	7°	9°